L Number	Hits	Search Text	DB	Time stamp
6	6949	((sensor) near (piezoel ctric or	USPAT;	2004/04/15
		piezo-electric or piezo))	US-PGPUB;	17:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	1243	(((sensor) near (piezoelectric or	USPAT;	2004/04/15
•		piezo-electric or piezo))) and displacement	US-PGPUB;	16:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	4	(((sensor) near (piezoelectric or	USPAT;	2004/04/15
_		piezo-electric or piezo))) and (micrometer	US-PGPUB;	16:40
		near displacement)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	33	(((sensor) near (piezoelectric or	USPAT;	2004/04/15
•		piezo-electric or piezo))) and (small near	US-PGPUB;	16:41
		displacement)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	4826	(strain near sensor)	USPAT;	2004/04/15
	4020	(ortain nodi concor)	US-PGPUB;	17:21
			EPO; JPO;	••••
			DERWENT;	
			IBM_TDB	
11	703	((strain near sensor)) and (micro micron)	USPAT;	2004/04/15
••	, , ,		US-PGPUB;	17:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	8	((strain near sensor)) near (micro micron)	USPAT;	2004/04/15
		((0.00.00.00.00.00.00.00.00.00.00.00.00.	US-PGPUB;	17:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	2	((strain near sensor)) and ((micro micron)	USPAT;	2004/04/15
	_	near meter)	US-PGPUB;	17:18
		mountaily	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	5	((strain near sensor)) and ((micrometer	USPAT;	2004/04/15
	J	micron) near (displace displacement))	US-PGPUB;	17:22
		incidity floar (alepiace alepiacellicity)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	28853	(strain near gauge)	USPAT;	2004/04/15
	2000	(Calair ileat gauge)	US-PGPUB;	17:50
			EPO; JPO;	17.50
			DERWENT;	
			IBM_TDB	

and the same of th			
19	((strain near gauge)) and ((micrometer	USPAT;	2004/04/15
	micron) near (displace displacement))	US-PGPUB;	17:56
		EPO; JPO;	
		DERWENT;	
		IBM_TDB	
5220	(measurement) n ar (displace	USPAT;	2004/04/15
	displacement)	US-PGPUB;	17:24
1		EPO; JPO;	
		DERWENT;	
		IBM_TDB	
31574	(strain near (sensor gauge))	USPAT;	2004/04/15
		US-PGPUB;	17:55
		EPO; JPO;	
		DERWENT;	
		IBM_TDB	
352	((measurement) near (dispiace	USPAT;	2004/04/15
	displacement)) and ((strain near (sensor	US-PGPUB;	17:50
		EPO; JPO;	
		DERWENT;	
•		IBM_TDB	
4004	(strain near tensile)	1 -	2004/04/15
		1	17:50
		•	
		1	
23	((measurement) near (displace		2004/04/15
			17:55
		EPO; JPO;	
		DERWENT;	
		IBM_TDB	
35223	(strain near (sensor gauge tensile))	USPAT;	2004/04/15
		US-PGPUB;	17:55
	·	EPO; JPO;	
		DERWENT;	
		IBM_TDB	
366	((measurement) near (displace	USPAT;	2004/04/15
	,,	US-PGPUB;	17:55
1	gauge tensile)))	EPO; JPO;	
	<i></i>	DERWENT;	
		IBM_TDB	
8	(((measurement) near (displace	USPAT;	2004/04/15
		US-PGPUB;	17:57
	gauge tensile)))) and ((milimeter	EPO; JPO;	
		DERWENT;	
		IBM_TDB	
36	-	USPAT;	2004/04/15
		1	18:25
		DERWENT;	
	5220 31574 352 4004 23 35223	micron) near (displace displacement)) 5220 (measurement) n ar (displace displacement) 31574 (strain near (sensor gauge)) 352 ((measurement) near (displace displacement)) and ((strain near (sensor gauge))) 4004 (strain near tensile) 23 ((measurement) near (displace displacement)) and ((strain near tensile)) 35223 (strain near (sensor gauge tensile)) 366 ((measurement) near (displace displacement)) and ((strain near (sensor gauge tensile))) 8 (((measurement) near (displace displacement)) and ((strain near (sensor gauge tensile)))) and ((millimeter micrometer micron) near (displace displacement))	micron) near (displace displacement)) ### S220 ### Comparison of the process of

		T .:	T	T
26	376	(((sens r) near (piezoelectric r	USPAT;	2004/04/15
		piezo-electric or plezo))) and (high near	US-PGPUB;	18:25
		sensitivity)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
27	82	((((sensor) near (piezoelectric r	USPAT;	2004/04/15
		piezo-electric or plezo))) and (high near	US-PGPUB;	18:26
		sensitivity)) and (micrometer milimeter	EPO; JPO;	
		micron)	DERWENT;	
			IBM_TDB	
28	7	(((((sensor) near (piezoelectric or	USPAT;	2004/04/15
		piezo-electric or piezo))) and (high near	US-PGPUB;	18:27
		sensitivity)) and (micrometer milimeter	EPO; JPO;	
		micron)) and ((tensile force forced) near	DERWENT;	
		(gauge probe strain sensor))	IBM_TDB	
•	1	chun-keng near hsu	USPAT;	2002/11/04
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	tin-hau near kuo	USPAT;	2002/11/04
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	chun-chih near lin	USPAT;	2002/11/04
			US-PGPUB;	10:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	2	chao-lin near lee	USPAT;	2002/11/04
			US-PGPUB;	10:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	432	wafer near blade	USPAT;	2002/11/04
			US-PGPUB;	11:15
			EPO; JPO;	
			DERWENT;	
		*	IBM_TDB	
	1128713	sensor	USPAT;	2002/11/04
			US-PGPUB;	13:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3798	sensor near strain	USPAT;	2002/11/04
			US-PGPUB;	10:38
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	

•	787	(sensor near strain) and (piezoelectric or	USPAT;	2002/11/04
		piezo-electric or piezo)	US-P PUB;	10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	+
_	73	(sens r near strain) near (piezoelectric r	USPAT:	2002/11/04
		piezo-electric or piezo)	US-PGPUB;	10:39
		piczo cicotiio oi piczo,	EPO; JPO;	-
			DERWENT;	
			IBM_TDB	
	0	(wafer near blade) and ((sensor near strain)	USPAT;	2002/11/04
-		· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	10:39
		and (piezoelectric or piezo-electric or	•	10:39
		piezo))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	134	(wafer near blade) and sensor	USPAT;	2002/11/04
			US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10	((wafer near blade) and sensor) and	USPAT;	2002/11/04
		(piezoelectric)	US-PGPUB;	11:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7	("4610475" "4642438" "4667997"	USPAT	2002/11/04
		"5100502" "5438419" "5511931"		11:11
		"5641264").PN.		
_	3	"6113165"	USPAT	2002/11/04
_				11:11
_	21	("4040736" "4093378" "5044752"	USPAT	2002/11/04
-		"5103367" "5173832" "5400209"	JOI A.	11:11
		"5436790" "5444342" "5444597"		
		"5445486" "5556147" "5645391"		
		"5669752" "5841515" "5842491"		
		"5863170" "5867359" "5872694"		
		"5885355" "5903123" "5948986").PN.	Hera	2002/44/04
•	4471	wafer near chuck	USPAT;	2002/11/04
			US-PGPUB;	11:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	170	(wafer near chuck) and (piezoelectric)	USPAT;	2002/11/04
			US-PGPUB;	11:15
	İ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	97	((wafer near chuck) and (piezoelectric)) and	USPAT;	2002/11/04
		sensor	US-PGPUB;	11:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	77	(((wafer near chuck) and (piezoelectric))	USPAT;	2002/11/04
		and sensor) and (alarm signal)	US-P PUB;	13:23
		, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	3	(((wafer near chuck) and (piez electric))	USPAT;	2002/11/04
		and sensor) and (alarm)	US-PGPUB;	13:24
		and sensor , and (alarm)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	134	(wafer near blade) and sensor	USPAT;	2002/11/04
_	134	(Water field bidde) and sensor	US-PGPUB;	13:30
			EPO; JPO;	10.00
			DERWENT;	
			IBM_TDB	
	7	((wafer near blade) and sensor) and alarm	USPAT;	2002/11/04
·	'	((Water flear blade) and sensor) and alarm	US-PGPUB;	13:30
			EPO; JPO;	13.30
			1	•
			DERWENT;	
		.4	IBM_TDB	2002/11/04
•	5358	strain near gage	USPAT;	14:56
1			US-PGPUB;	14:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/44/04
-	878	(strain near gage) and (wafer	USPAT;	2002/11/04
		semiconductor)	US-PGPUB;	14:56
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/44/04
•	1424	(strain near (sensor or gage)) and (wafer	USPAT;	2002/11/04
		semiconductor)	US-PGPUB;	14:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/44/24
-	68	(strain near (sensor or gage)) and (wafer	USPAT;	2002/11/04
		semiconductor) and blade	US-PGPUB;	14:58
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/00/15
•	2	("6494882").PN.	USPAT;	2003/08/12
			US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	28565	strain near (sensor gauge)	USPAT;	2003/08/12
			US-PGPUB;	12:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

[•	605	(wafer semiconductor) near blade	USPAT;	2003/08/12
			US-PGPUB;	12:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	465244	thin same film	USPAT;	2003/08/12
			US-PGPUB;	12:46
			EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	
_	4	(strain near (sensor gauge)) and ((wafer	USPAT;	2003/08/12
	•	semiconductor) near blade)	US-PGPUB;	12:48
		Semiconductory medical biddey	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	5007		_	2003/08/12
-	5807	piezoelectric near (sensor sensing	USPAT;	12:49
		sensitive)	US-PGPUB;	143
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	584	(strain near (sensor gauge)) and	USPAT;	2003/08/12
		(piezoelectric near (sensor sensing	US-PGPUB;	12:50
		sensitive))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	("4502857" "5043111" "5174933"	USPAT	2003/08/12
		"5528452" "6294113").PN.		13:31
-	145	(73/767).CCLS.	USPAT;	2003/08/25
			US-PGPUB;	13:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	17035	sensitivity and 73/\$.ccls.	USPAT;	2003/08/25
			US-PGPUB;	13:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	468	(sensitivity and 73/\$.ccls.) and (strain near	USPAT;	2003/08/25
	-700	sensor)	US-PGPUB;	13:15
		sensor,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	460060	73/\$.ccls.	USPAT;	2003/08/25
-	162268	/ J/#.CCIS.	· · · · · · · · · · · · · · · · · · ·	15:56
			US-PGPUB;	13:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/07
-	4339	strain near sensor	USPAT;	2003/08/25
			US-PGPUB;	13:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	975	73/\$.ccls. and (strain near sensor)	USPAT;	2003/08/25
			US-PGPUB;	13:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	468	sensitivity and (73/\$.ccls. and (strain n ar	USPAT;	2003/08/25
		sensor))	US-PGPUB;	13:42
			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
	18832	(touch contact) near sensor	USPAT;	2003/08/25
			US-PGPUB;	16:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
l <u>.</u>	46	(73/\$.ccls. and (strain near sensor)) and	USPAT;	2003/08/25
-		((touch contact) near sensor)	US-PGPUB;	13:43
		Wisach contact hear sensor	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	020	(//sough southers) uses source) and misrou	USPAT;	2003/08/25
-	928	((touch contact) near sensor) and micron	US-PGPUB;	15:56
			1	15:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/05
-	10	(strain near sensor) and (((touch contact)	USPAT;	2003/08/25
		near sensor) and micron)	US-PGPUB;	13:52
			EPO; JPO;	:
			DERWENT;	
			IBM_TDB	
-	77270	414/\$.ccis.	USPAT;	2003/08/25
			US-PGPUB;	16:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	22990	(strain touch contact) near sensor	USPAT;	2003/08/25
			US-PGPUB;	15:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	220	414/\$.ccls. and ((strain touch contact) near	USPAT;	2003/08/25
		sensor)	US-PGPUB;	16:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	(414/\$.ccls. and ((strain touch contact) near	USPAT;	2003/08/25
		sensor)) and micron	US-PGPUB;	15:58
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	12	("4449885" "4520421" "4565601"	USPAT	2003/08/25
		"4743570" "4892451" "4911597"		16:03
		"4962441" "4999507" "5007981"		
		"5113992" "5258047" "5315473").PN.		
-	36806	294/\$.ccls.	USPAT;	2003/08/25
			US-PGPUB;	16:06
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	51	294/\$.ccls. and ((strain touch contact) near	USPAT;	2003/08/25
		sensor)	US-PGPUB;	16:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	5822	wafer near (blade chuck gripper)	USPAT;	2003/08/25
			US-PGPUB;	16:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
l <u>-</u>	49	(wafer near (blade chuck gripper)) and	USPAT;	2003/08/25
		((strain touch contact) near sensor)	US-PGPUB;	16:11
		((bitain touch contact) hour conser,	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
	29618	strain near (sensor gauge)	USPAT;	2003/08/25
-	29010	Strain near (sensor gauge)	US-PGPUB;	17:33
			EPO; JPO;	17.33
			DERWENT;	
			IBM_TDB	2003/08/25
-	5606	sensitivity same micron	USPAT;	
			US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/07
•	94	(strain near (sensor gauge)) and (sensitivity	USPAT;	2003/08/25
		same micron)	US-PGPUB;	17:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	116	(73/768).CCLS.	USPAT;	2003/08/25
			US-PGPUB;	17:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	524	piezo-electric near sensor	USPAT;	2003/08/25
			US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

			HCDAT-	2002/00/0=
-	60	(strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezo-electric near sensor)	US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2222/22/27
-	1	((strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezo-electric near sensor)) and micron	US-PGPUB;	17:43
			EPO; JPO;	
			DERWENT;	
ļ			IBM_TDB	
-	5260	piezoelectric near sensor	USPAT;	2003/08/25
			US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	578	(strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezoelectric near sensor)	US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	143	((strain near (sensor gauge)) and	USPAT;	2003/08/25
		(piezoelectric near sensor)) and	US-PGPUB;	17:49
		(semiconductor wafer)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	145	(73/769).CCLS.	USPAT;	2003/08/25
İ			US-PGPUB;	18:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	60	(73/770).CCLS.	USPAT;	2003/08/25
			US-PGPUB;	18:17
			EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
-	622	(semiconductor wafer) near blade	USPAT;	2003/10/17
			US-PGPUB;	14:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1399972	(semiconductor wafer)	USPAT;	2003/10/17
			US-PGPUB;	14:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	110214	((semiconductor wafer)) and sensor	USPAT;	2003/10/17
			US-PGPUB;	14:43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	7687	(((semiconductor wafer)) and s nsor) and	USPAT;	2003/10/17
		strain	US-P PUB; EP ; JPO; DERWENT; IBM_TDB	14:43
-	1985	((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:44
-	7	(((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 294/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:54
	35	("Re28663" "1315581" "3353860" "3370213" "3491520" "3625378" "3827437" "4130314" "4540211" "4544193" "4552397" "4565400" "4579380" "4590673" "4610475" "4667997" "4671553" "4694230" "4696501" "4699414" "4723806" "4735451" "4796357" "4808898" "4813732" "4816730" "4819978" "4828309" "4872803" "4898416" "4955656" "4976484" "5046773" "5080415" "5163804").PN.	USPAT	2003/10/17 14:49
-	13	(((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 414/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:02
-	7	("4610475" "4642438" "4667997" "5100502" "5438419" "5511931" "5641264").PN.	USPAT	2003/10/17 14:59
-	50	(((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 29/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:14
-	10	("4674186" "5266801" "5325081" "5345815" "5386720" "5400647" "5468959" "5469733" "5907095" "6072247").PN.	USPAT	2003/10/17 15:06
-	502	(((((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 73/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:15

123 (((((((((((((((((((((((((((((((((((
and 73/\$.ccis.) and micro EPQ; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM, TDB USPAT; US-PGPUB; ISM, TDB USPAT; US-PGPUB; ISM, TDB USPAT; US-PGPUB; ISM, TDB USPAT; US-PGPUB; ISM,	•	123	1	•	
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO;			1	•	15:15
10800 plez electric near (layer sensor) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; U			and 73/\$.ccls.) and micro	EPO; JPO;	
10800 piez electric near (layer sensor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US				DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;				IBM_TDB	
Company	-	10800	piez electric near (layer sensor)	USPAT;	2003/10/17
- 622 (wafer semiconductor) near blade USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISPAT; US-PGPUB; EPO; JPO; DERWENT; ISPAT; US-PGPUB; EPO; JPO; DERWENT; IFAT US-PGPUB; IFAT US-PGPUB; IFAT US-PGPUB; IFAT US-PGPUB; IFAT US-PGPUB; IFAT US-PG				US-PGPUB;	17:41
BM_TDB				EPO; JPO;	
. 622 (wafer semiconductor) near blade USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; IFO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; JP				DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;				IBM_TDB	
A	-	622	(wafer semiconductor) near blade	USPAT;	2003/10/17
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IMB_TDB USPAT; US-PGPUB				US-PGPUB;	17:40
A				EPO; JPO;	
4				DERWENT;	
((wafer semiconductor) near blade) ((wafer semiconductor) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISPAT; US-PGPUB;				IBM_TDB	
((wafer semiconductor) near blade) ((wafer semiconductor) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISPAT; US-PGPUB;	-	4	(piezoelectric near (layer sensor)) and		2003/10/17
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IB			1 "		17:15
- 1399972 (wafer semiconductor) - 1399972 (wafer semiconductor) - 2089 (piezoelectric near (layer sensor)) and (logicoelectric near (layer sensor)) and (logic			, ,	EPO; JPO;	
1399972 (wafer semiconductor) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; USPAT; US-PGPUB; USPAT; US-PGPUB;					
- 1399972 (wafer semiconductor) - 1399972 (wafer semiconductor) - 2089 (piezoelectric near (layer sensor)) and ((wafer semiconductor)) - 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor)) - 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) USPAT; 2003/10/17 17:21 EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;				IBM TDB	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; IFO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; IFO; JPO; JPO; DERWENT; JPO; JPO; DERWENT; JPO; JPO	_	1399972	(wafer semiconductor)	_	2003/10/17
- 2089 (piezoelectric near (layer sensor)) and ((wafer semiconductor)) - 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IFOB USPAT; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-			(care and a care a		17:20
- 2089 (piezoelectric near (layer sensor)) and ((wafer semiconductor)) - 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor)	-			•	
- 2089 (piezoelectric near (layer sensor)) and ((wafer semiconductor)) - 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) - 496 (((piezoelectric near (layer sensor))) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor)) and (micron micrometer)) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor)	ł			, ,	
- 2089 (piezoelectric near (layer sensor)) and ((wafer semiconductor)) - 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and ((wafer semiconductor))) and (micron micrometer)) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor) - 14601 piezoelectric near (film layer sensor)	i				
((wafer semiconductor)) ((wafer semiconductor)) ((piezoelectric near (layer sensor)) and (logs semiconductor)) and (micron micrometer) ((wafer semiconductor))) and (micron micrometer) ((piezoelectric near (layer sensor)) and (logs semiconductor)) and (logs semiconductor)) and (micron micrometer)) and thin ((wafer semiconductor)) and (micron micrometer)) and thin ((wafer semiconductor)) and (micron micrometer)) and thin (wafer semiconductor) near (grip gripper handler holder blade)	_	2089	(piezoelectric near (laver sensor)) and	_	2003/10/17
EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; USPGPUB; U	ļ		1 -	•	17:20
- 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISPO; JPO; DERWENT; ISPO; JPO; DERWENT; IF:42			"	1	
- 611 ((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer) - 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) 14601				· · · · · · · · · · · · · · · · · · ·	
((wafer semiconductor))) and (micron micrometer) 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin 496 ((wafer semiconductor))) and (micron micrometer)) and thin 496 (wafer semiconductor))) and (micron micrometer)) and thin 496 (wafer semiconductor) near (grip gripper handler holder blade) 496 (wafer semiconductor) near (grip gripper handler holder blade) 497 (wafer semiconductor) near (grip gripper handler holder blade) 497 (wafer semiconductor) near (grip gripper handler holder blade) 498 (wafer semiconductor) near (grip gripper handler holder blade) 499 (wafer semiconductor) near (grip gripper handler holder blade) 499 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 499 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder				IBM_TDB	
((wafer semiconductor))) and (micron micrometer) 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin 496 ((wafer semiconductor))) and (micron micrometer)) and thin 496 (wafer semiconductor))) and (micron micrometer)) and thin 496 (wafer semiconductor) near (grip gripper handler holder blade) 496 (wafer semiconductor) near (grip gripper handler holder blade) 497 (wafer semiconductor) near (grip gripper handler holder blade) 497 (wafer semiconductor) near (grip gripper handler holder blade) 498 (wafer semiconductor) near (grip gripper handler holder blade) 499 (wafer semiconductor) near (grip gripper handler holder blade) 499 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 499 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder blade) 490 (wafer semiconductor) near (grip gripper handler holder	-	611	((piezoelectric near (layer sensor)) and	USPAT;	2003/10/17
micrometer) - 496 (((piezoelectric near (layer sensor)) and (USPAT; IBM_TDB (Wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IF-PO; JPO; DERWENT; JPO; DERWENT; JPO; JPO; DERWENT; JPO; JPO; DERWENT; JPO; JPO; DERWENT; JPO; JPO; DERWENT; J			1	US-PGPUB;	17:21
- 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	ļ		1,1		
- 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IS-PGPUB; EPO; JPO; DERWENT; EPO; DERWEN					
- 496 (((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin - 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;				•	
((wafer semiconductor))) and (mlcron micrometer)) and thin 8680 (wafer semiconductor) near (grip gripper handler holder blade) (wafer semiconductor) near (grip gripper handler holder blade) 14601 piezoelectric near (film layer sensor) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	496	(((piezoelectric near (layer sensor)) and		2003/10/17
micrometer)) and thin EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			1		
- 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-			· ·	
- 8680 (wafer semiconductor) near (grip gripper handler holder blade) - 14601 piezoelectric near (film layer sensor) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			"		
- 8680 (wafer semiconductor) near (grip gripper handler holder blade) - USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 14601 piezoelectric near (film layer sensor) USPAT; USPAT; USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT;				,	
handler holder blade) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	8680	(wafer semiconductor) near (grip gripper		2003/10/17
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;			1	,	
- 14601 piezoelectric near (film layer sensor) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;			,	•	
- 14601 piezoelectric near (film layer sensor) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				, ,	
- 14601 piezoelectric near (film layer sensor) USPAT; 2003/10/17 US-PGPUB; 17:42 EPO; JPO; DERWENT;					
US-PGPUB; 17:42 EPO; JPO; DERWENT;	-	14601	piezoelectric near (film laver sensor)	_	2003/10/17
EPO; JPO; DERWENT;					
DERWENT;					
	1				
				IBM_TDB	

	5501	(piezoelectric near (film layer sensor)) and	USPAT;	2003/10/17
		thin	US-PGPUB;	17:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	24	((wafer semiconductor) near (grip gripper	USPAT;	2003/10/17
		handler holder blade)) and ((piezoelectric	US-PGPUB;	17:45
		near (film layer sensor)) and thin)	EPO; JPO;	
			DERWENT;	
ı			IBM_TDB	
-	27	((wafer semiconductor) near (grip gripper	USPAT;	2003/10/17
		handler holder blade)) and (piezoelectric	US-PGPUB;	17:45
		near (film layer sensor))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1256	((piezoelectric near (film layer sensor)) and	USPAT;	2003/10/17
		thin) and (micron micrometer)	US-PGPUB;	17:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	663	(((piezoelectric near (film layer sensor)) and	USPAT;	2003/10/17
		thin) and (micron micrometer)) and sensor	US-PGPUB;	17:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	663	((((piezoelectric near (film layer sensor))	USPAT;	2003/10/17
		and thin) and (micron micrometer)) and	US-PGPUB;	17:47
1		sensor) and thin	EPO; JPO;	
			DERWENT;	
	1	444	IBM_TDB	2002/40/47
-	487	((((piezoelectric near (film layer sensor))	USPAT;	2003/10/17
		and thin) and (micron micrometer)) and	US-PGPUB;	18:59
		sensor) and (thin near (layer film))	EPO; JPO; DERWENT;	
			IBM_TDB	
	2	("6469421").PN.	USPAT;	2003/10/17
	_	(0703721 /11111	US-PGPUB;	18:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	("5681410" "6103072" "6284434"	USPAT	2003/10/17
		"6332254").PN.		18:59